

Yiming Wang

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	High-Performance Phototransistors by Alumina Encapsulation of a 2D Semiconductor with Self-Aligned Contacts. <i>Advanced Electronic Materials</i> , 2022, 8, .	5.1	5
2	Comparative Study of Short-Channel Effects Between Source-Gated Transistors and Standard Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 561-566.	3.0	7
3	Frequency Division Multiplexer With Directional Filters in Multilayer LCP Films at - and -Band. <i>IEEE Microwave and Wireless Components Letters</i> , 2022, 32, 1287-1290.	3.2	3
4	Self-powered UV photodetectors and imaging arrays based on NiO/IGZO heterojunctions fabricated at room temperature. <i>Optics Express</i> , 2022, 30, 27453.	3.4	9
5	Thin Film Sequential Circuits: Flip-Flops and a Counter Based on p-SnO and n-InGaZnO. <i>IEEE Electron Device Letters</i> , 2021, 42, 62-65.	3.9	9
6	SnO _x -Based W-Power Dual-Gate Ion-Sensitive Thin-Film Transistors With Linear Dependence of pH Values on Drain Current. <i>IEEE Electron Device Letters</i> , 2021, 42, 54-57.	3.9	1
7	In Situ Growth of GeS Nanowires with Sulfur-Rich Shell for Featured Negative Photoconductivity. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 3046-3052.	4.6	14
8	Imaging Array and Complementary Photosensitive Inverter Based on P-Type SnO Thin-Film Phototransistors. <i>IEEE Electron Device Letters</i> , 2021, 42, 1010-1013.	3.9	8
9	Active terahertz metamaterials electrically modulated by InGaZnO Schottky diodes. <i>Optical Materials Express</i> , 2021, 11, 2966.	3.0	9
10	Multi frequency multi bit amplitude modulation of spoof surface plasmon polaritons by schottky diode bridged interdigital SRRs. <i>Scientific Reports</i> , 2021, 11, 19181.	3.3	7
11	High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO ₂ Anode. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 4444-4449.	3.0	7
12	Schottky-barrier thin-film transistors based on HfO ₂ -capped InSe. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	13
13	Tunable Surface Plasmon Polaritons with Monolithic Schottky Diodes. <i>ACS Applied Electronic Materials</i> , 2019, 1, 2124-2129.	4.3	13
14	High-Performance InGaZnO-Based ReRAMs. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2600-2605.	3.0	18
15	Extremely high-gain source-gated transistors. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2019, 116, 4843-4848.	7.1	58
16	Reconfigurable Spoof Surface Plasmon Polariton Band-stop Filter with Monolithic Schottky Diodes. , 2019, , .		1
17	Complementary Integrated Circuits Based on p-Type SnO and n-Type IGZO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2018, 39, 208-211.	3.9	48
18	Amorphous-InGaZnO Thin-Film Transistors Operating Beyond 1 GHz Achieved by Optimizing the Channel and Gate Dimensions. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 1377-1382.	3.0	32

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19	Highly Optimized Complementary Inverters Based on p-SnO and n-InGaZnO With High Uniformity. IEEE Electron Device Letters, 2018, 39, 516-519.	3.9	35
20	Oxide-Based Complementary Inverters With High Gain and Nanowatt Power Consumption. IEEE Electron Device Letters, 2018, 39, 1676-1679.	3.9	23
21	All-Oxide-Semiconductor-Based Thin-Film Complementary Static Random Access Memory. IEEE Electron Device Letters, 2018, 39, 1876-1879.	3.9	7
22	Influence of interface inhomogeneities in thin-film Schottky diodes. Applied Physics Letters, 2017, 111, 213503.	3.3	15